

NTTFS4930N

MOSFET – Power, Single, N-Channel, μ 8FL

30 V, 23 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- Power Load Switch
- Notebook Battery Management
- Motor Control

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	30	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	I_D	7.2	A
	$T_A = 85^\circ\text{C}$		5.2	
Power Dissipation $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	P_D	2.06	W
	$T_A = 85^\circ\text{C}$			
Continuous Drain Current $R_{\theta JA} \leq 10$ s (Note 1)	$T_A = 25^\circ\text{C}$	I_D	9.6	A
	$T_A = 85^\circ\text{C}$		6.9	
Power Dissipation $R_{\theta JA} \leq 10$ s (Note 1)	$T_A = 25^\circ\text{C}$	P_D	3.61	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	I_D	4.5	A
	$T_A = 85^\circ\text{C}$		3.2	
Power Dissipation $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	P_D	0.79	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	I_D	23	A
	$T_C = 85^\circ\text{C}$		16	
Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	P_D	20.2	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10$ μs	I_{DM}	92	A
Operating Junction and Storage Temperature		T_J , T_{stg}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	25	A
Drain to Source dV/dt		dV/dt	6.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 50$ V, $V_{GS} = 10$ V, $I_L = 12$ A_{pk} , $L = 0.1$ mH, $R_G = 25$ Ω)		E_{AS}	7.2	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

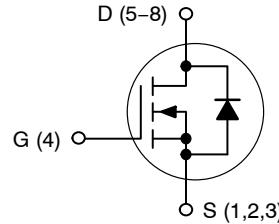


ON Semiconductor®

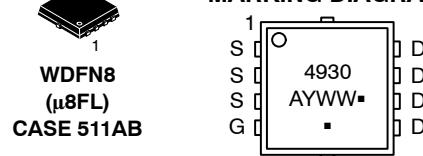
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	23 m Ω @ 10 V	
	30 m Ω @ 4.5 V	23 A

N-Channel MOSFET



MARKING DIAGRAM



4930 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NTTFS4930NTAG	WDFN8 (Pb-Free)	1500/Tape & Reel
NTTFS4930NTWG	WDFN8 (Pb-Free)	5000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTTFS4930N

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	6.2	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	60.7	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	159	
Junction-to-Ambient – ($t \leq 10$ s) (Note 3)	$R_{\theta JA}$	34.6	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
4. Surface-mounted on FR4 board using the minimum recommended pad size (40 mm², 1 oz. Cu).

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$			16		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 24 \text{ V}$	$T_J = 25^{\circ}\text{C}$		1.0	μA
			$T_J = 125^{\circ}\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = \pm 20 \text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 250 \mu\text{A}$	1.2	1.6	2.2	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$			3.7		$\text{mV}/^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 7 \text{ A}$		15	23
			$I_D = 10 \text{ A}$		15	
		$V_{\text{GS}} = 4.5 \text{ V}$	$I_D = 6 \text{ A}$		22.7	30
			$I_D = 10 \text{ A}$		22.7	
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 1.5 \text{ V}, I_D = 15 \text{ A}$		19		s

CHARGES AND CAPACITANCES

Input Capacitance	C_{iss}	$V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}, V_{\text{DS}} = 15 \text{ V}$		476		pF
Output Capacitance	C_{oss}			197		
Reverse Transfer Capacitance	C_{rss}			101		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 4.5 \text{ V}, V_{\text{DS}} = 15 \text{ V}, I_D = 20 \text{ A}$		5.6		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			0.5		
Gate-to-Source Charge	Q_{GS}			1.5		
Gate-to-Drain Charge	Q_{GD}			2.5		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 15 \text{ V}, I_D = 20 \text{ A}$		10.3		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = 4.5 \text{ V}, V_{\text{DS}} = 15 \text{ V}, I_D = 15 \text{ A}, R_G = 3.0 \Omega$		8.4		ns
Rise Time	t_r			26.6		
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$			10.4		
Fall Time	t_f			3.6		

5. Pulse Test: pulse width = 300 μs , duty cycle $\leq 2\%$.
6. Switching characteristics are independent of operating junction temperatures.

NTTFS4930N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 15\text{ V}$, $I_D = 15\text{ A}$, $R_G = 3.0\ \Omega$	4.6		ns
Rise Time	t_r		17.6		
Turn-Off Delay Time	$t_{d(off)}$		13.3		
Fall Time	t_f		2.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}$, $I_S = 20\text{ A}$	$T_J = 25^\circ\text{C}$	0.97	1.2	V
			$T_J = 125^\circ\text{C}$	0.89		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}$, $dI_S/dt = 100\text{ A}/\mu\text{s}$, $I_S = 20\text{ A}$		15.3		ns
Charge Time	t_a			7.4		
Discharge Time	t_b			7.9		
Reverse Recovery Charge	Q_{RR}			4.6		nC

PACKAGE PARASITIC VALUES

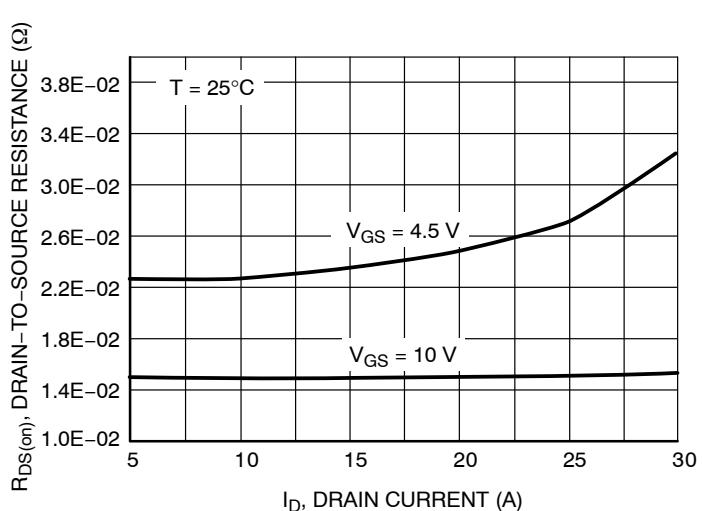
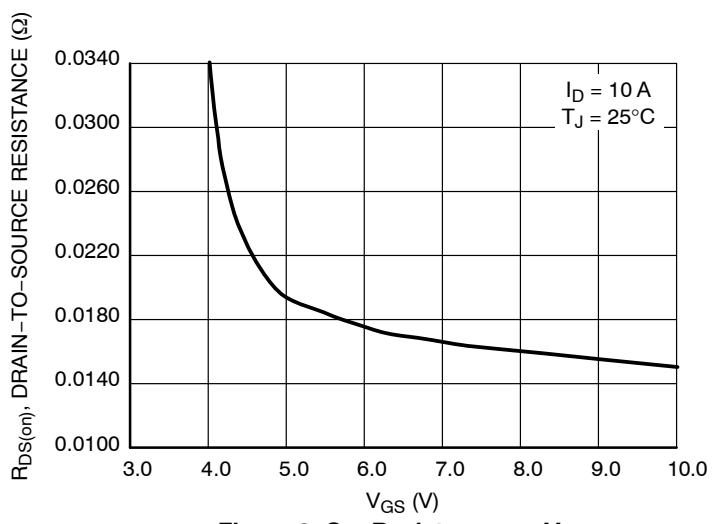
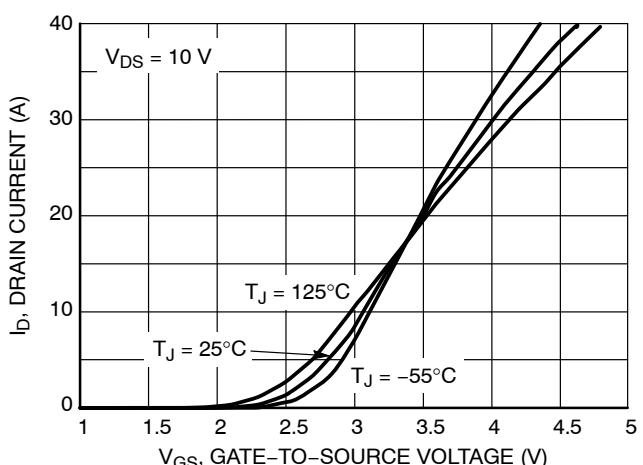
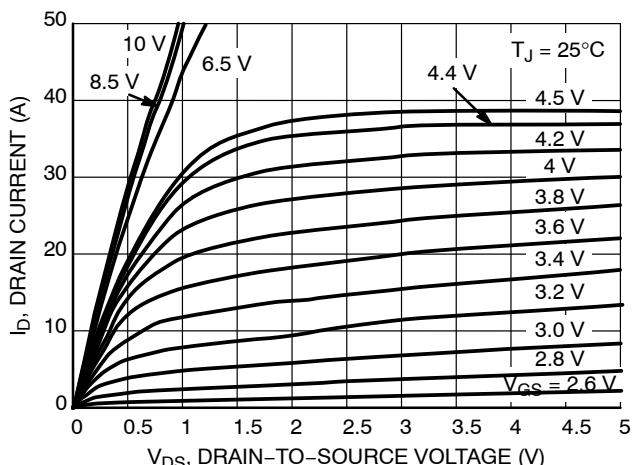
Source Inductance	L_S	$T_A = 25^\circ\text{C}$	0.38		nH
Drain Inductance	L_D		0.054		
Gate Inductance	L_G		1.3		
Gate Resistance	R_G		0.6		Ω

5. Pulse Test: pulse width = 300 μs , duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTTFS4930N

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

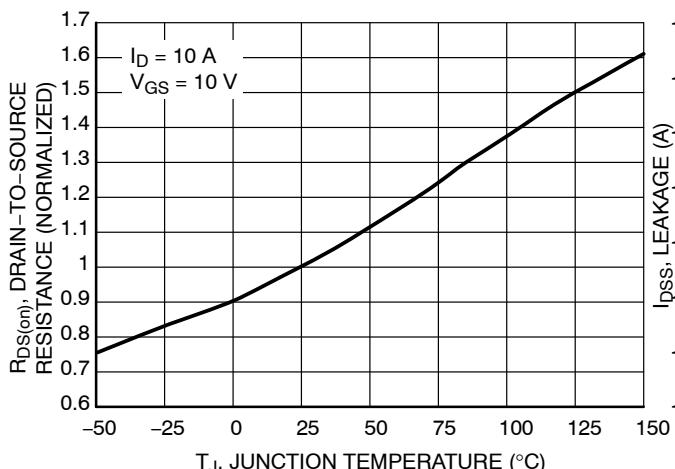


Figure 5. On-Resistance Variation with Temperature

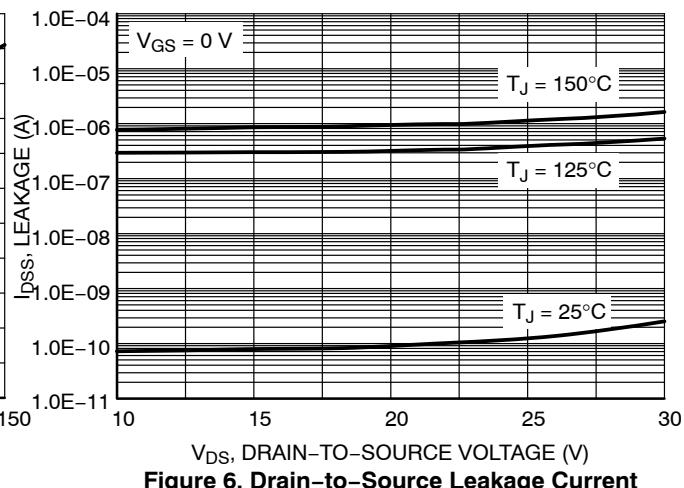


Figure 6. Drain-to-Source Leakage Current vs. Voltage

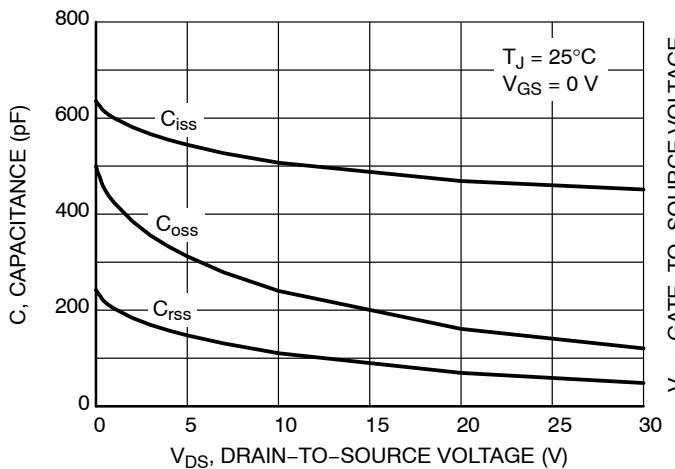


Figure 7. Capacitance Variation

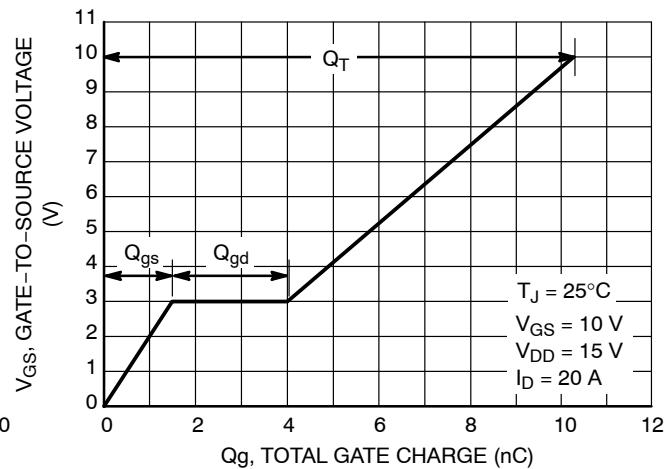


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

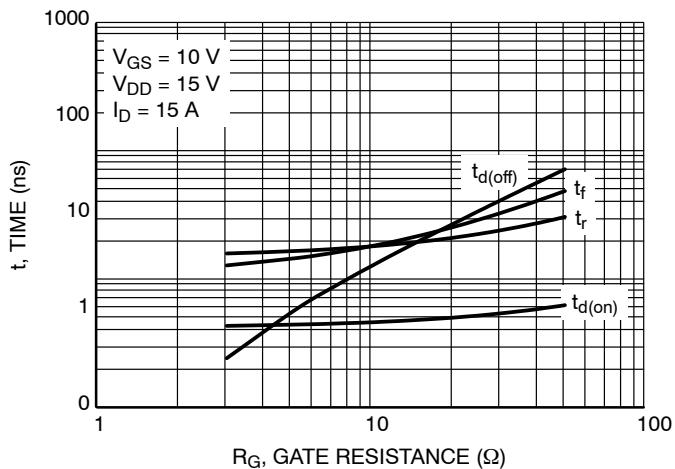


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

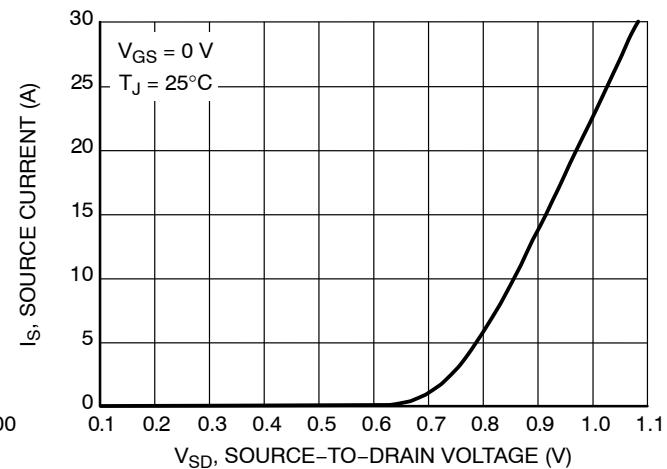


Figure 10. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

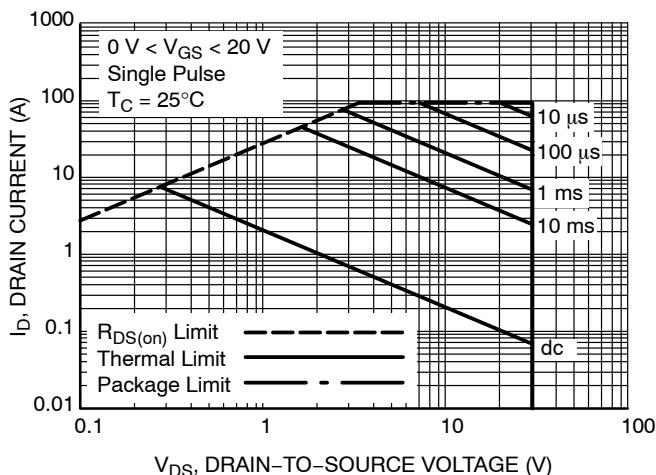


Figure 11. Maximum Rated Forward Biased Safe Operating Area

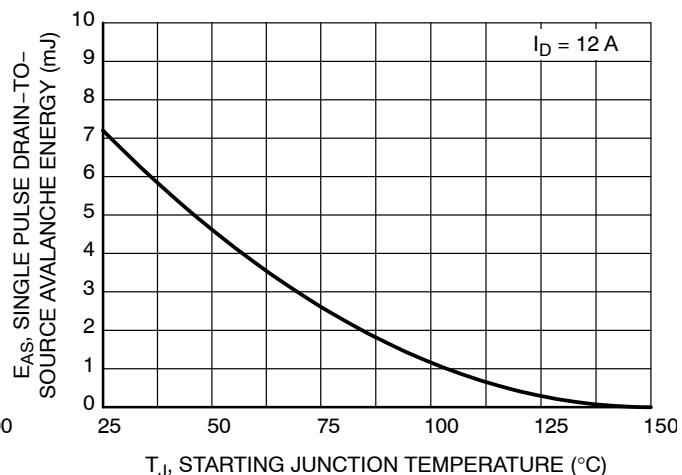


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

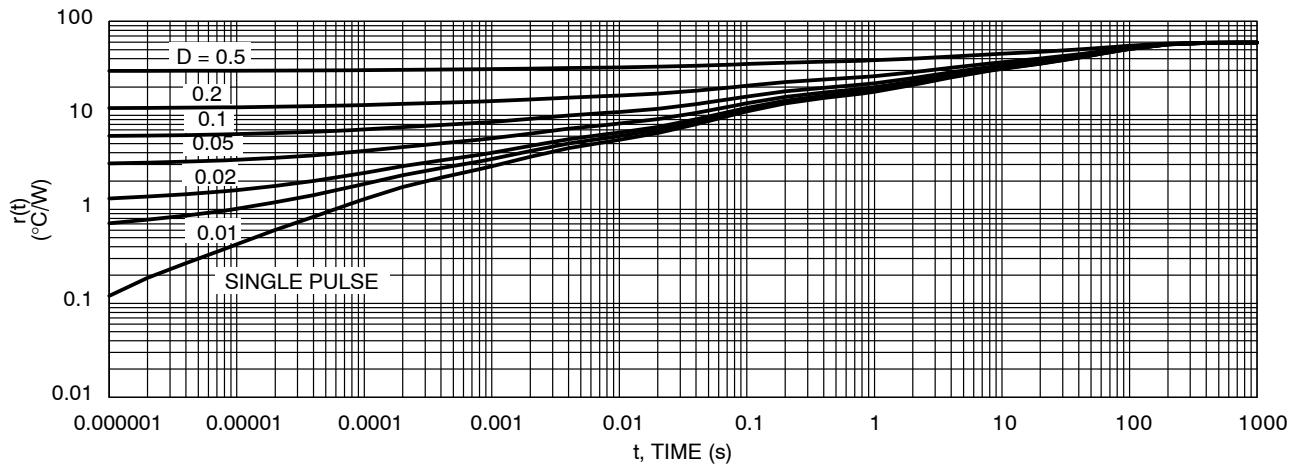


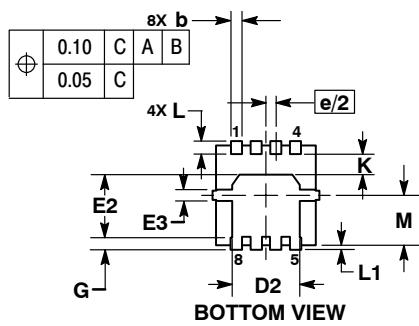
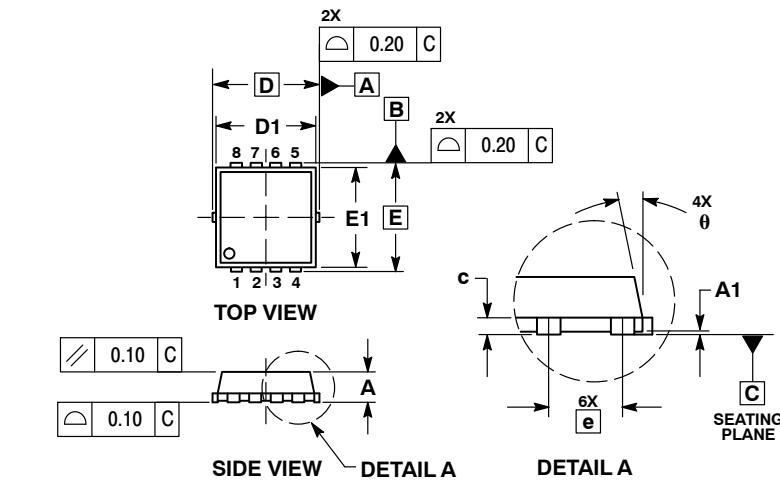
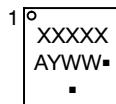
Figure 13. Thermal Response



SCALE 2:1

WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

DATE 23 APR 2012

GENERIC
MARKING DIAGRAM*

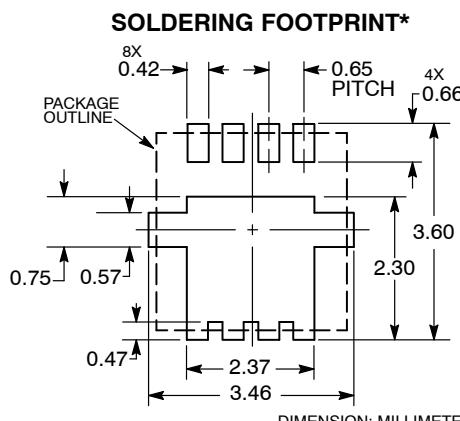
XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30	BSC	3.30	0.130	BSC	0.130
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30	BSC	3.30	0.130	BSC	0.130
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65	BSC	0.65	0.026	BSC	0.026
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0	°	---	12	°	0



*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON30561E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	WDFN8 3.3X3.3, 0.65P	PAGE 1 OF 1

onsemi and **Onsemi** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, **ONSEMI**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

